Analog Power AM4438N

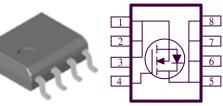
N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low r_{DS(on)} and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
V _{DS} (V)	$r_{\mathrm{DS}(\mathrm{on})} \mathrm{m}(\Omega) \qquad \qquad \mathrm{I}_{\mathrm{D}} (A)$			
30	$32 @ V_{GS} = 4.5V$	8.1		
	$40 @ V_{GS} = 2.5V$	7.2		

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage			30	V	
Gate-Source Voltage			±8	V	
	T _A =25°C]] _{T_}	±8.1		
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	±6.6	A	
Pulsed Drain Current ^b			±50		
Continuous Source Current (Diode Conduction) ^a		I_S	2.3	A	
D a	$T_A=25^{\circ}C$	D	3.1	W	
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	l _L D	2.2	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C	

HALOGEN **FREE**

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
	t <= 10 sec	D	50	°C/W		
Maximum Junction-to-Ambient ^a	Steady State	$R_{ heta JA}$	92	°C/W		

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Notes

- Surface Mounted on 1" x 1" FR4 Board. a.
- Pulse width limited by maximum junction temperature b.

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SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
D		T . C . W.	Limits			TT
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{(BR)DSS}$ $V_{GS} = 0 \text{ V}, I_D = 250 \text{ uA}$				3 7
Gate-Threshold Voltage	V _{GS(th)}	$V_{\rm DS} = V_{\rm GS},I_{\rm D} = 250\mathrm{uA}$	1.0		1.5	V
Gate-Body Leakage	Igss	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA
Zaro Cata Valtaga Drain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	
On-State Drain Current ^A	ID(on)	$V_{DS} = 5 \text{ V}, V_{GS} = \pm 8 \text{ V}$	8			A
Dig G D i A	fDS(on)	$V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$	32		32	
Drain-Source On-Resistance ^A		$V_{GS} = 2.5 \text{ V}, I_D = 2 \text{ A}$			40	mΩ
Forward Tranconductance ^A	gfs	$V_{DS} = 15 \text{ V}, I_{D} = 2 \text{ A}$		40		S
Diode Forward Voltage	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V
Dynamic ^b						
Total Gate Charge	Qg	V 15 V V 45 V		7		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		2		nC
Gate-Drain Charge	Q_{gd}	$I_D = 9 A$		3]
Turn-On Delay Time	td(on)			10		
Rise Time	t _r	$V_{\rm DD} = 25 \text{ V}, R_{\rm L} = 25 \Omega \text{ , Id} = 1 \text{ A},$ $V_{\rm GEN} = 10 \text{ V}$		12		nS
Turn-Off Delay Time	td(off)			25		
Fall-Time	tf			11		

Notes

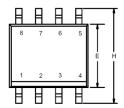
a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

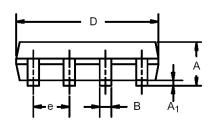
b. Guaranteed by design, not subject to production testing.

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Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

